

Features

Package TO252

- Built-in zener Di between collector gate VCL typ. 400V
- · Built-in gate protection diode
- · SMD PKG TO252
- · Low saturated voltage

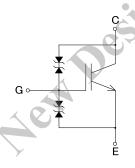
VCE(sat) Max. 1.4V (at VGE=10V, IC=5A)



Applications

Equivalent circuit

Ignitor



Absolute maximum ratings

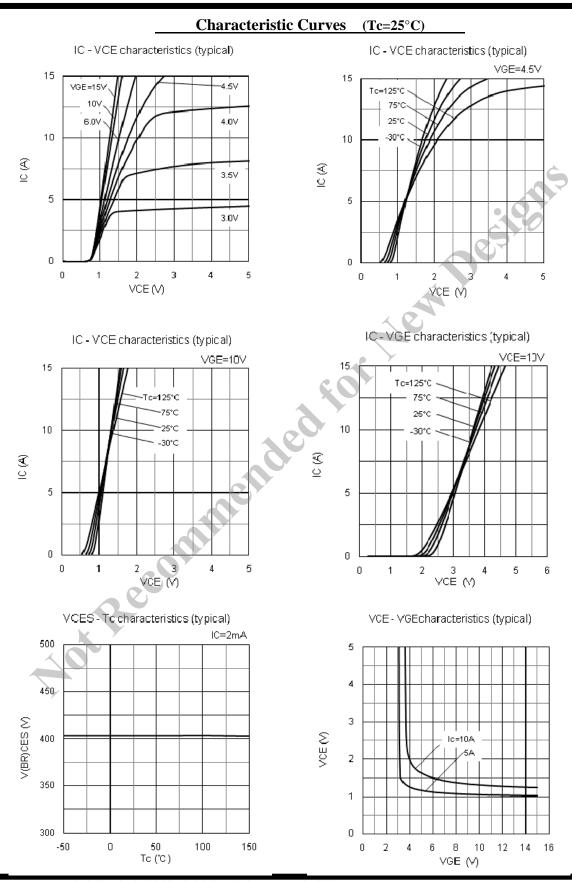
Absolute maximum ratings								
	6	(Ta=25°C)					
Characteristic	Symbol	Rating	Unit					
Collector to Emitter Voltage	VCES	CLAMPED	V					
Gate to Emitter Voltage	VGE	± 20	V					
Continuous Collector Current	IC(DC)	15	A					
Maximum Allowable Power Dissipation	PC	55 (Tc=25°C)	W					
Operating Junction Temperature	Tj	150	°C					
Storage Temperature	Tstg	-55 to +150	°C					

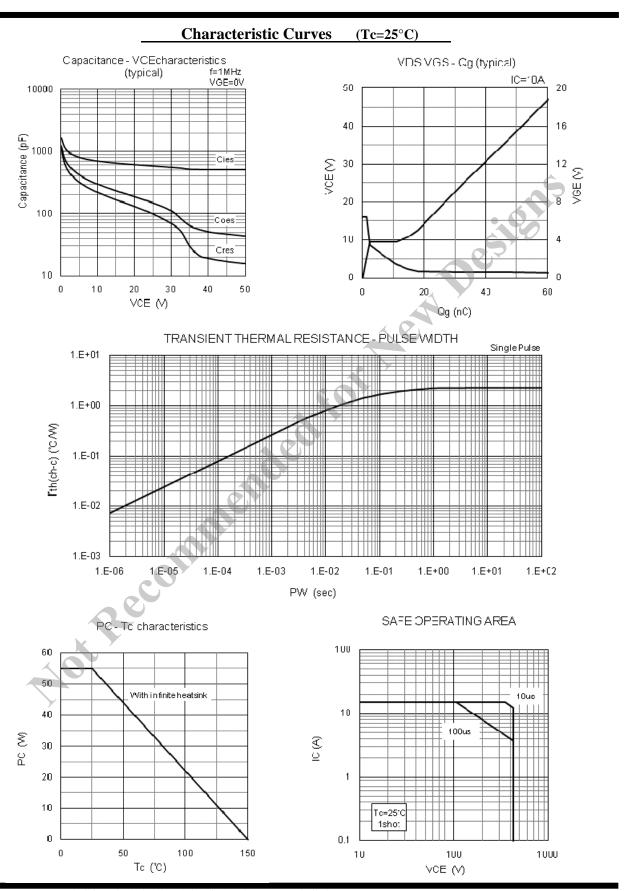


Electrical characteristics

(Ta=25°C)

at	Symbol			23 ()		
Characteristic		Test Conditions	MIN.	TYP.	MAX.	Unit
Collector to Emitter Breakdown Voltage	V(BR)CES	IC= 2mA, VGE=0V	375	400	425	V
Gate to Emitter Breakdown Voltage	V(BR)GES	IG=±100μA, VCE=0V	±20		05	V
Emitter to Collector Breakdown Voltage	V(BR)ECS	IEC=10mA, VGE=0V	20		Ö	V
Collector to Emitter Leakage Current	ICES	VCE=300V, VGE=0V)	100	μΑ
Gate to Emitter Leakage Curren	IGES	VGE=±20V,VCE=0V			±100	μΑ
Gate Threshold Voltage	VGE(th)	VCE=10V, IC=1mA	1.4	1.8	2.2	V
Collector to Emitter Saturation Voltage	VCE(sat)	VGE=4.5V, IC= 5A		1.2	1.5	V
Collector to Emitter Saturation Voltage	VCE(sat)	VGE=10V, IC= 5A		1.1	1.4	V
Collector to Emitter Saturation Voltage	VCE(sat)	VGE=10V, IC= 10A		1.4	1.7	V
Input Capacitance	Cies			700		
Output Capacitance	Coes	VCE=10V f=1.0MHz VGE=0V		300		pF
Reverse Transfer Capacitance	Cres			220		
Self Clamped Inductive Switching Energy	Es/B	L=5mH, Rg=200Ω	150			mJ





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